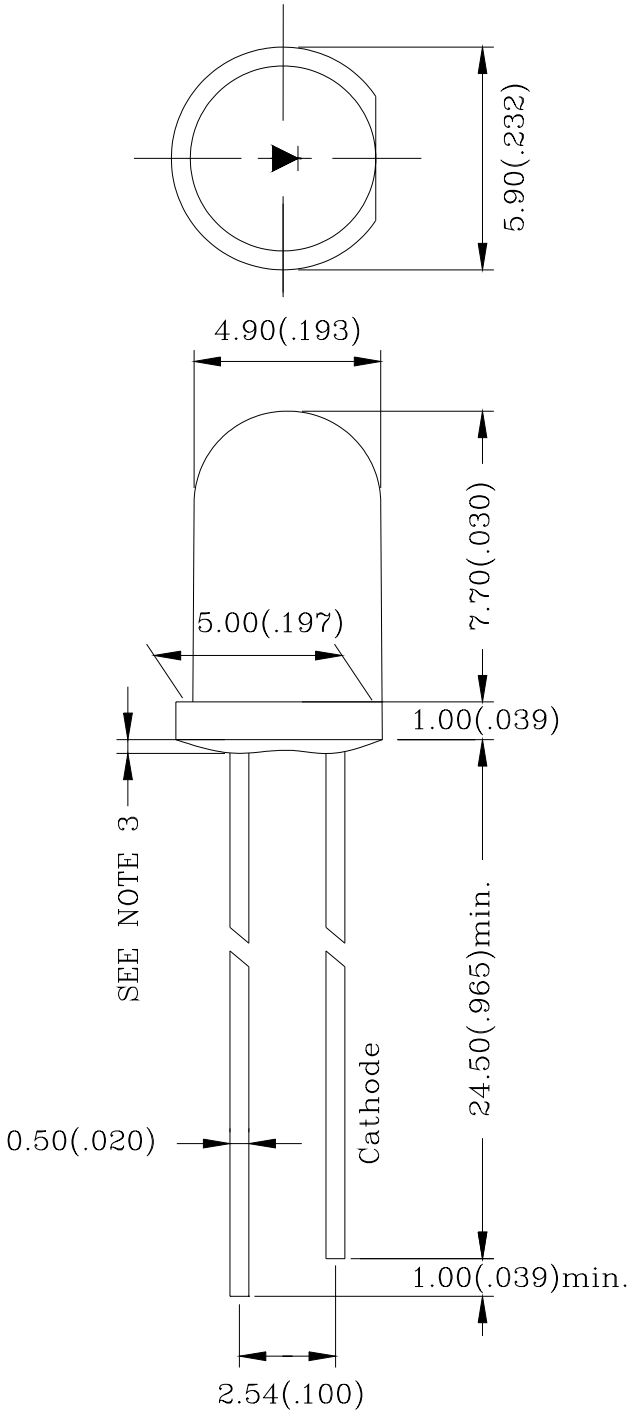
SYC SEMICONDUCTORES Y COMPONENTES

LED-010-50045

PACKAGE DIMENSIONS



Note:

1.All Dimensions are in millimeters.

2.Tolerance is ±0.25mm(0.010 ")
Unless otherwise specified.

3.Protruded resin under flange
is 1.5mm(0.059 ") max.

4.Lead spacing is measured where
the leads emerge from the package.

5.Specification are subject to change
without notice

6.highlight <-400V the led can
withstand the max static level when
assembling or operation.

5.0 mm DIA LED LAMP

FEATURES

* SUITABLE HIGH PULSE CURRENT OPERATION
* EXTRA HIGH RADIANT POWER AND RADIANT INTENSITY
* HIGH RELIABILITY
* LOW FORWARD VOLTAGE

CHIP MATERIALS

* Dice Material : GaInN/GaN
* Light Color : BLUEGREEN
* Lens Color : WATER CLEAR

ABSOLUTE MAXIMUM RATING:(Ta＝25°C)

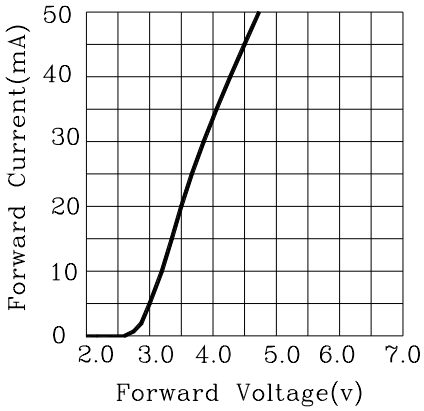
SYMBOL	DESCRIPTION	BLUE-GREEN	UNIT
P_{AD}	Power Dissipation Per Chip	120	mW
V_R	Reverse Voltage Per Chip	5	V
I_F	Average Forward Current Per Chip	30	mA
-	Derating Linear From 25°C Per Chip	0.4	mA/°C
Topr	Operating Temperature Range	-25°C to 85°C	
Tstg	Storage Temperature Range	-40°C to 85°C	
Lead Soldering Temperature｛1.6mm(0.063 inch) From Body｝		260°C±5°C For 5 Seconds	

ELECTRO-OPTICAL CHARACTERISTICS:(Ta=25°C)

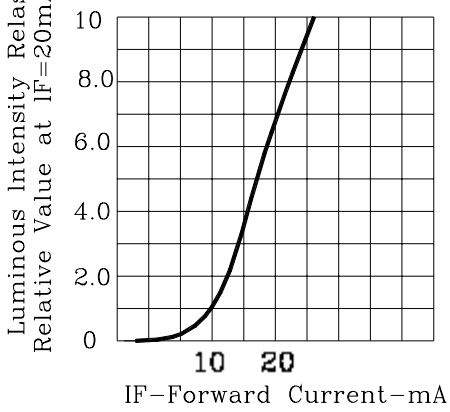
SYMBOL	DESCRIPTION	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
V_F	Forward Voltage	I_F = 20mA		3.5	4.0	V
I_R	Reverse Current	V_R = 5V			100	μA
λ_D	Dominant Wavelength	I_F = 20mA		505		nm
$\Delta\lambda$	Spectral Line Half-Width	I_F = 20mA		22		nm
2θ1/2	Half Intensity Angle	I_F = 20mA		20		deg
I_V	Luminous Intensity	I_F = 20mA		6500	8000	mcd

5.0 mm DIA LED LAMP

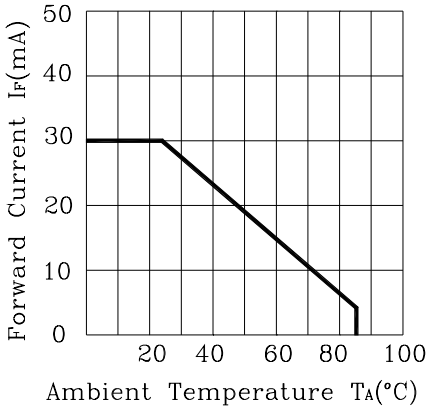
Forward Current Vs
Forward Voltage



Luminous Intensity VS.
(cd) Forward Current



Forward Current
Derating Curve



Luminous Intensity VS.
Ambient Temperature

